

### CoolSiC™ 1200 V SiC Trench MOSFET : Silicon Carbide MOSFET with .XT interconnection technology

#### Features

- $V_{DSS} = 1200\text{ V}$  at  $T_{vj} = 25^\circ\text{C}$
- $I_{DDC} = 70\text{ A}$  at  $T_c = 25^\circ\text{C}$
- $R_{DS(on)} = 30\text{ m}\Omega$  at  $V_{GS} = 18\text{ V}$ ,  $T_{vj} = 25^\circ\text{C}$
- Very low switching losses
- Short circuit withstand time  $3\ \mu\text{s}$
- Benchmark gate threshold voltage,  $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance

#### Potential applications

- General purpose drives (GPD)
- EV-Charging
- Online UPS/Industrial UPS
- String inverters
- Solar power optimizer

#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

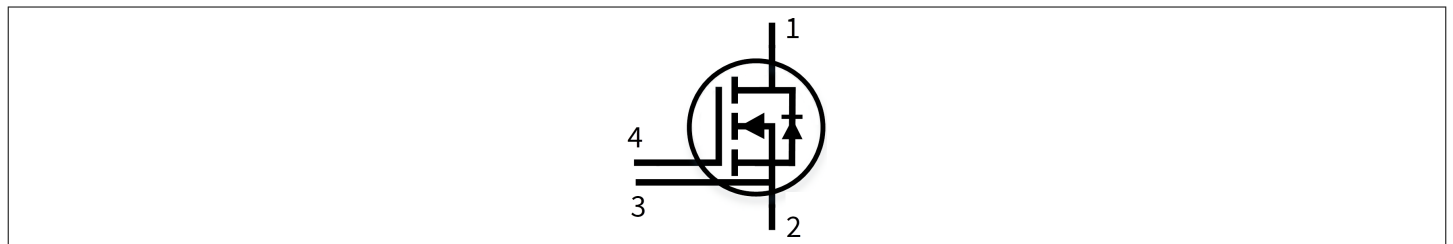


- Lead-Free
- Green
- Halogen-Free
- RoHS

#### Description

- 1 – drain
- 2 – source
- 3 – Kelvin sense contact
- 4 – gate

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



Type	Package	Marking
IMZA120R030M1H	PG-TO247-4-STD-NT3.7	12M1H030

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## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	$M$	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W

## 2 MOSFET

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	$V_{DSS}$	$T_{vj} \geq 25\text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$ , limited by $T_{vj(max)}$	$I_{DDC}$	$V_{GS} = 18\text{ V}$	$T_c = 25\text{ °C}$	70	A
			$T_c = 100\text{ °C}$	49	
Peak drain current, $t_p$ limited by $T_{vj(max)}$	$I_{DM}$	$V_{GS} = 18\text{ V}$	147	A	
Gate-source voltage, max. transient voltage <sup>1)</sup>	$V_{GS}$	$t_p \leq 0.5\ \mu\text{s}$ , $D < 0.01$	-10/23	V	
Gate-source voltage, max. static voltage	$V_{GS}$		-7/20	V	
Avalanche energy, single pulse	$E_{AS}$	$I_D = 25\text{ A}$ , $V_{DD} = 50\text{ V}$ , $L = 1.4\text{ mH}$	450	mJ	
Avalanche energy, repetitive	$E_{AR}$	$I_D = 25\text{ A}$ , $V_{DD} = 50\text{ V}$ , $L = 7.1\ \mu\text{H}$	2.23	mJ	
Short-circuit withstand time	$t_{SC}$	$V_{DD} \leq 800\text{ V}$ , $V_{DS,peak} < 1200\text{ V}$ , $V_{GS(on)} = 15\text{ V}$ , $T_{vj(start)} = 25\text{ °C}$	3	$\mu\text{s}$	
Power dissipation, limited by $T_{vj(max)}$	$P_{tot}$	$T_c = 25\text{ °C}$	273	W	
		$T_c = 100\text{ °C}$	136		

1) Important note: The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in Application Note AN2018-09 must be considered to ensure sound operation of the device over the planned lifetime.

**Table 3** Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V

(table continues...)

**Table 3 (continued) Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

**Table 4 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 25.6 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$ , $V_{GS(on)} = 18 \text{ V}$		30	40.9	mΩ
			$T_{vj} = 100 \text{ }^\circ\text{C}$ , $V_{GS(on)} = 18 \text{ V}$		41		
			$T_{vj} = 175 \text{ }^\circ\text{C}$ , $V_{GS(on)} = 18 \text{ V}$		50		
			$T_{vj} = 25 \text{ }^\circ\text{C}$ , $V_{GS(on)} = 15 \text{ V}$		38	56	
Gate-emitter threshold voltage	$V_{GS(th)}$	$I_D = 11 \text{ mA}$ , $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$ )	$T_{vj} = 25 \text{ }^\circ\text{C}$	3.5	4.2	5.2	V
			$T_{vj} = 175 \text{ }^\circ\text{C}$		3.6		
Zero gate-voltage drain current	$I_{DSS}$	$V_{DS} = 1200 \text{ V}$ , $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			200	μA
			$T_{vj} = 175 \text{ }^\circ\text{C}$		3.4		
Gate leakage current	$I_{GSS}$	$V_{DS} = 0 \text{ V}$	$V_{GS} = 23 \text{ V}$			100	nA
			$V_{GS} = -10 \text{ V}$			-100	
Forward transconductance	$g_{fs}$	$I_D = 25.6 \text{ A}$ , $V_{DS} = 20 \text{ V}$		17.1		S	
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}$ , $V_{AC} = 25 \text{ mV}$		2.1		Ω	
Input capacitance	$C_{iss}$	$V_{DD} = 800 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 100 \text{ kHz}$ , $V_{AC} = 25 \text{ mV}$		2160		pF	
Output capacitance	$C_{oss}$	$V_{DD} = 800 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 100 \text{ kHz}$ , $V_{AC} = 25 \text{ mV}$		99		pF	
Reverse transfer capacitance	$C_{rss}$	$V_{DD} = 800 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 100 \text{ kHz}$ , $V_{AC} = 25 \text{ mV}$		14		pF	
$C_{oss}$ stored energy	$E_{oss}$	$V_{DD} = 800 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 100 \text{ kHz}$ , $V_{AC} = 25 \text{ mV}$		40		μJ	
Total gate charge	$Q_G$	$V_{DD} = 800 \text{ V}$ , $I_D = 25.6 \text{ A}$ , $V_{GS} = -2/18 \text{ V}$ , turn-on pulse		52		nC	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800 \text{ V}$ , $I_D = 25.6 \text{ A}$ , $V_{GS} = -2/18 \text{ V}$ , turn-on pulse		17		nC	
Gate-to-drain charge	$Q_{GD}$	$V_{DD} = 800 \text{ V}$ , $I_D = 25.6 \text{ A}$ , $V_{GS} = -2/18 \text{ V}$ , turn-on pulse		15		nC	

**(table continues...)**

**Table 4 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		23	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		22	
Rise time	$t_r$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		8.5	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		9.7	
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		27.3	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		28	
Fall time	$t_f$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		9.2	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		9.2	
Turn-on energy	$E_{on}$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		230	$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$		392	
Turn-off energy	$E_{off}$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		60	$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$		65	
Total switching energy	$E_{tot}$	$V_{DD} = 800\text{ V}, I_D = 25.6\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		330	$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$		618	

(table continues...)

**Table 4** (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.42	0.55	K/W
Virtual junction temperature	$T_{vj}$		-55		175	°C

Note: The chip technology was characterized up to 200 kV/μs. The measured  $dV/dt$  was limited by measurement test setup and package.

Dynamic test circuit see Fig. F.

### 3 Body diode

**Table 5** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	$V_{DSS}$	$T_{vj} \geq 25\text{ °C}$	1200	V	
Continuous reverse drain current for $R_{th(j-c,max)}$ , limited by $T_{vj(max)}$	$I_{SDC}$	$V_{GS} = 0\text{ V}$	$T_c = 25\text{ °C}$	66	A
			$T_c = 100\text{ °C}$	41	
Peak reverse drain current, $t_p$ limited by $T_{vj(max)}$	$I_{SM}$	$V_{GS} = 0\text{ V}$	147	A	

**Table 6** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source reverse voltage	$V_{SD}$	$I_{SD} = 25.6\text{ A}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		3.8	5	V
			$T_{vj} = 100\text{ °C}$		3.7		
			$T_{vj} = 175\text{ °C}$		3.6		
MOSFET forward recovery charge	$Q_{fr}$	$V_{DD} = 800\text{ V}, I_{SD} = 25.6\text{ A}, V_{GS} = 0\text{ V}, di_{SD}/dt = 3000\text{ A}/\mu\text{s}, Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ °C}$		210		nC
			$T_{vj} = 175\text{ °C}$		388		
MOSFET peak forward recovery current	$I_{frm}$	$V_{DD} = 800\text{ V}, I_{SD} = 25.6\text{ A}, V_{GS} = 0\text{ V}, di_{SD}/dt = 3000\text{ A}/\mu\text{s}, Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ °C}$		23		A
			$T_{vj} = 175\text{ °C}$		37		
MOSFET forward recovery energy	$E_{fr}$	$V_{DD} = 800\text{ V}, I_{SD} = 25.6\text{ A}, V_{GS} = 0\text{ V}, di_{SD}/dt = 3000\text{ A}/\mu\text{s}, Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ °C}$		40		μJ
			$T_{vj} = 175\text{ °C}$		161		

(table continues...)

**Table 6** (continued) Characteristic values

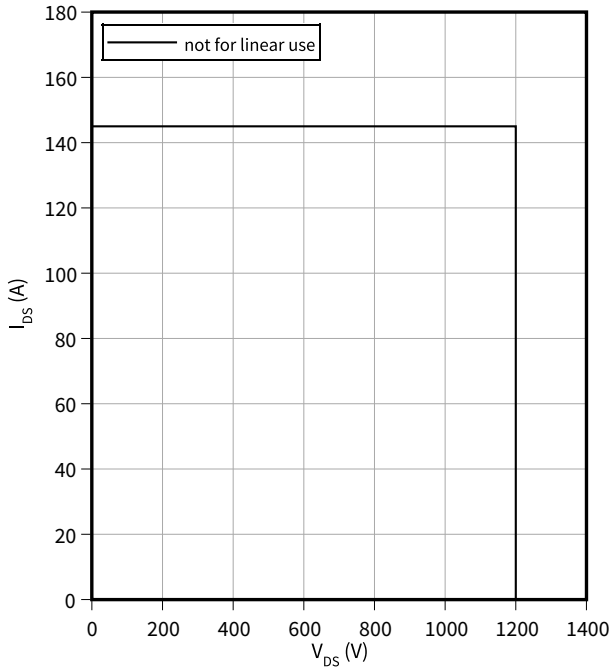
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.42	0.55	K/W
Virtual junction temperature	$T_{vj}$		-55		175	°C

## 4 Characteristics diagrams

### Reverse bias safe operating area (RBSOA)

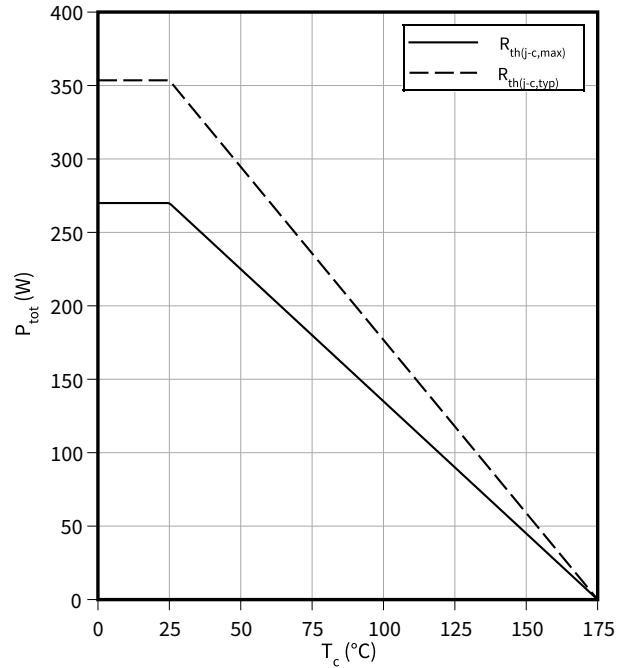
$$I_{DS} = f(V_{DS})$$

$$T_{vj} \leq 175\text{ °C}, V_{GS} = 0/18\text{ V}, T_c = 25\text{ °C}$$



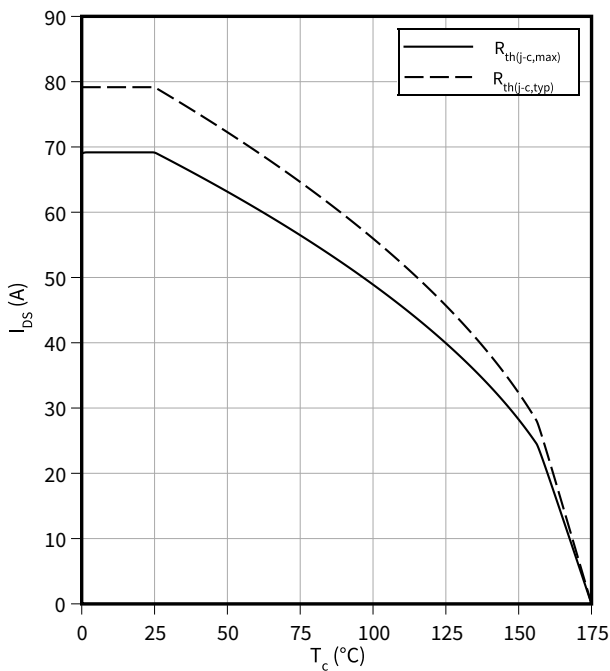
### Power dissipation as a function of case temperature limited by bond wire

$$P_{tot} = f(T_c)$$



### Maximum DC drain to source current as a function of case temperature limited by bond wire

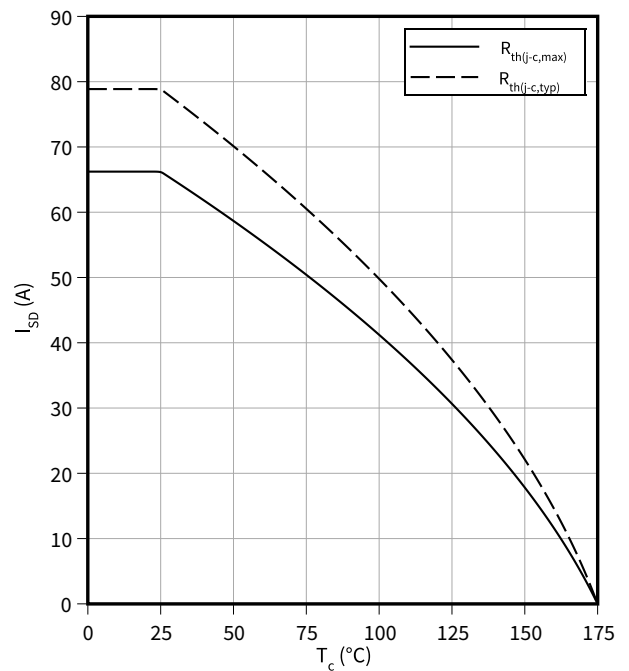
$$I_{DS} = f(T_c)$$



### Maximum source to drain current as a function of case temperature limited by bond wire

$$I_{SD} = f(T_c)$$

$$V_{GS} = 0\text{ V}$$

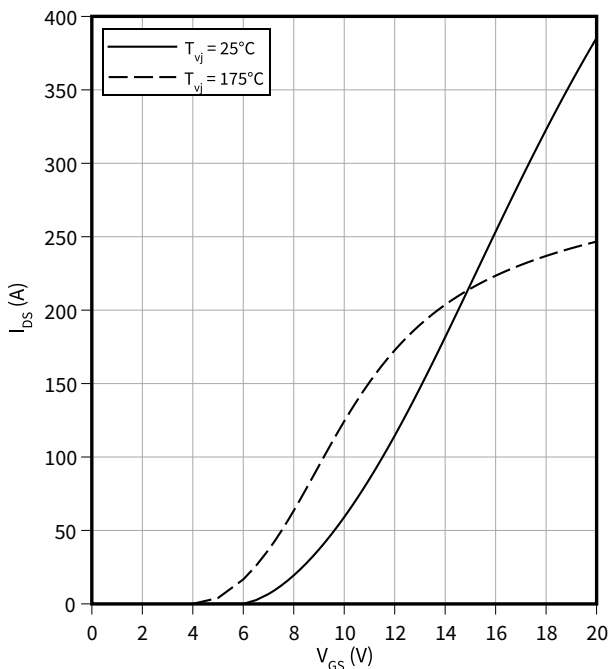




4 Characteristics diagrams

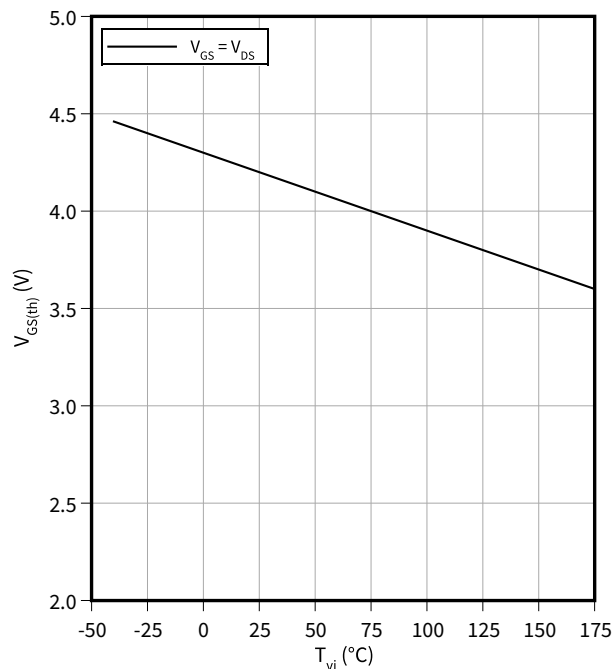
**Typical transfer characteristic**

$I_{DS} = f(V_{GS})$   
 $V_{DS} = 20\text{ V}$ ,  $t_p = 20\ \mu\text{s}$



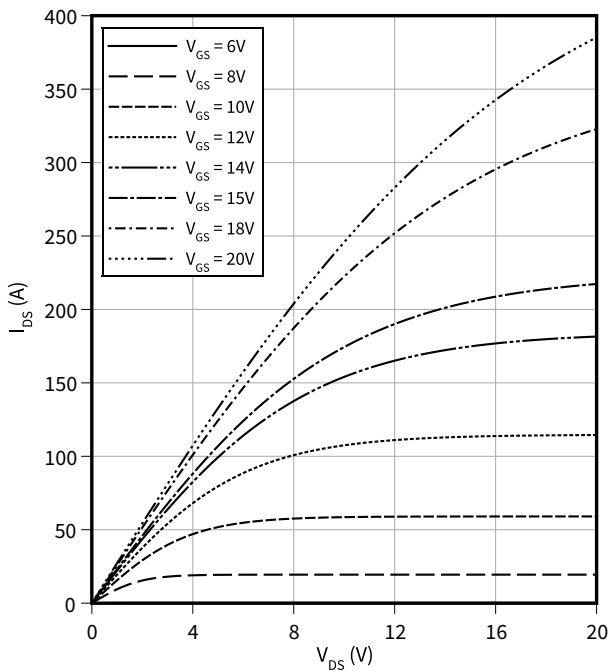
**Typical gate-source threshold voltage as a function of junction temperature**

$V_{GS(th)} = f(T_{vj})$   
 $I_D = 11\text{ mA}$



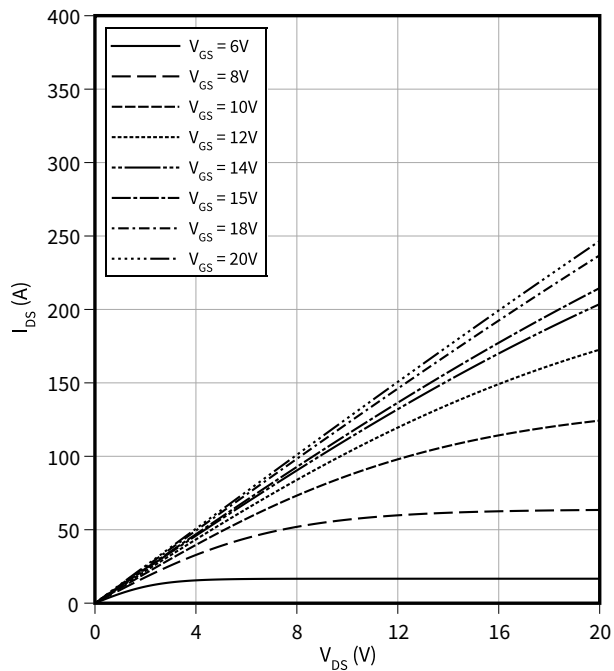
**Typical output characteristic,  $V_{GS}$  as parameter**

$I_{DS} = f(V_{DS})$   
 $T_{vj} = 25\ ^\circ\text{C}$ ,  $t_p = 20\ \mu\text{s}$



**Typical output characteristic,  $V_{GS}$  as parameter**

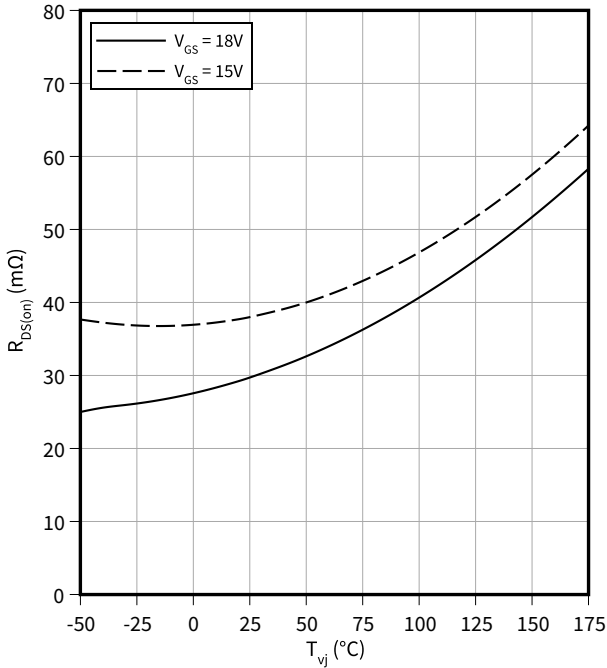
$I_{DS} = f(V_{DS})$   
 $T_{vj} = 175\ ^\circ\text{C}$ ,  $t_p = 20\ \mu\text{s}$



4 Characteristics diagrams

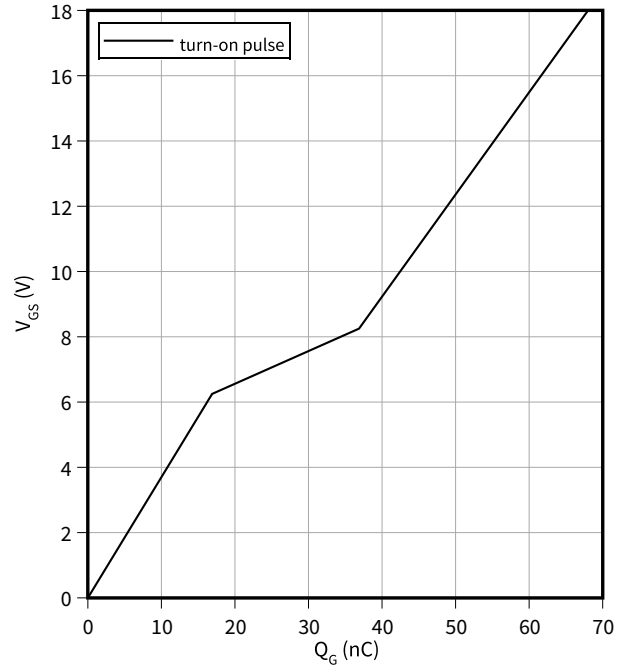
**Typical on-state resistance as a function of junction temperature**

$R_{DS(on)} = f(T_{vj})$   
 $I_D = 25.6 \text{ A}$



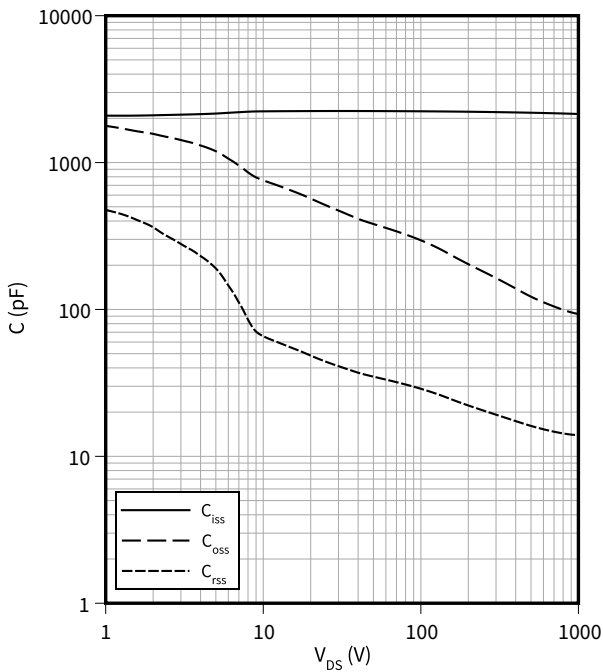
**Typical gate charge**

$V_{GS} = f(Q_G)$   
 $I_D = 25.6 \text{ A}, V_{DS} = 800 \text{ V}$



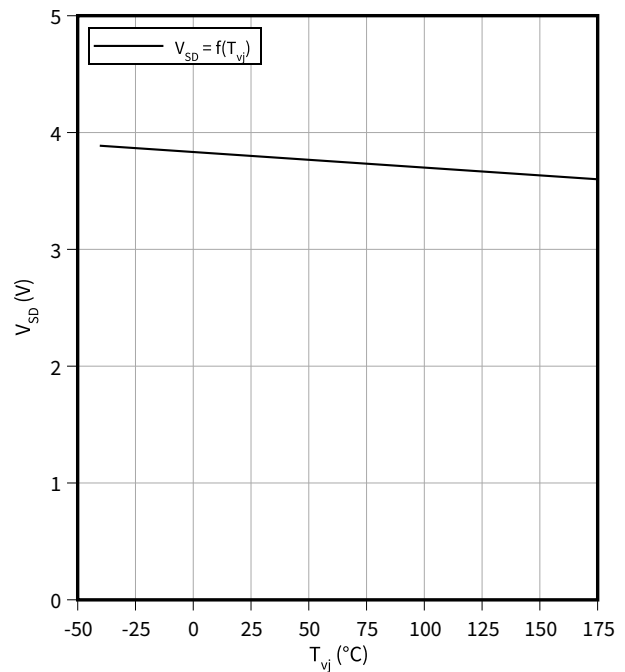
**Typical capacitance as a function of drain-source voltage**

$C = f(V_{DS})$   
 $f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



**Typical reverse drain voltage as function of junction temperature**

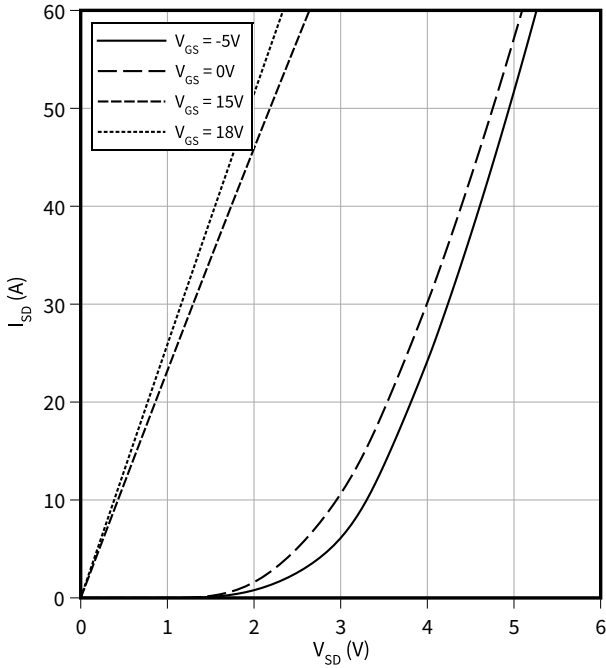
$V_{SD} = f(T_{vj})$   
 $I_{SD} = 25 \text{ A}, V_{GS} = 0 \text{ V}$



4 Characteristics diagrams

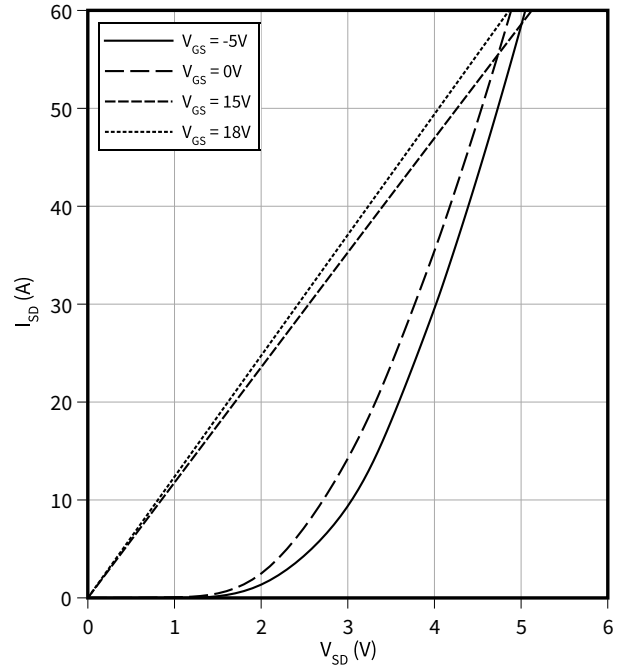
**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$   
 $T_{vj} = 25\text{ °C}$ ,  $t_p = 20\text{ }\mu\text{s}$



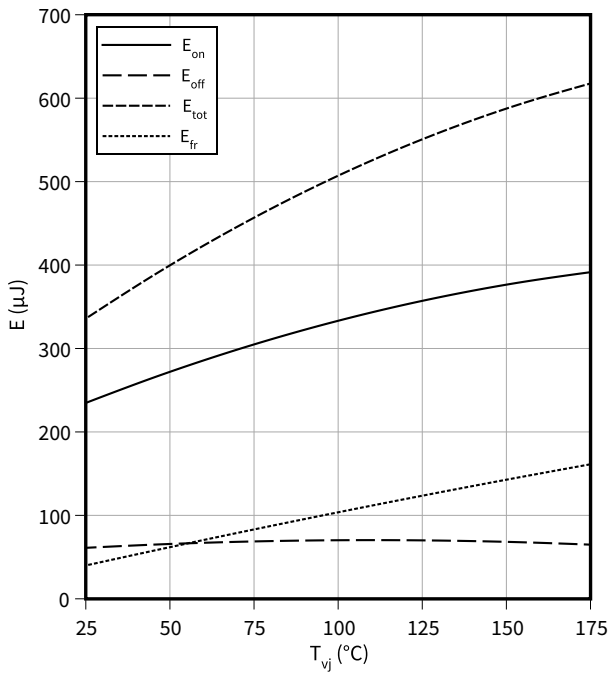
**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$   
 $T_{vj} = 175\text{ °C}$ ,  $t_p = 20\text{ }\mu\text{s}$



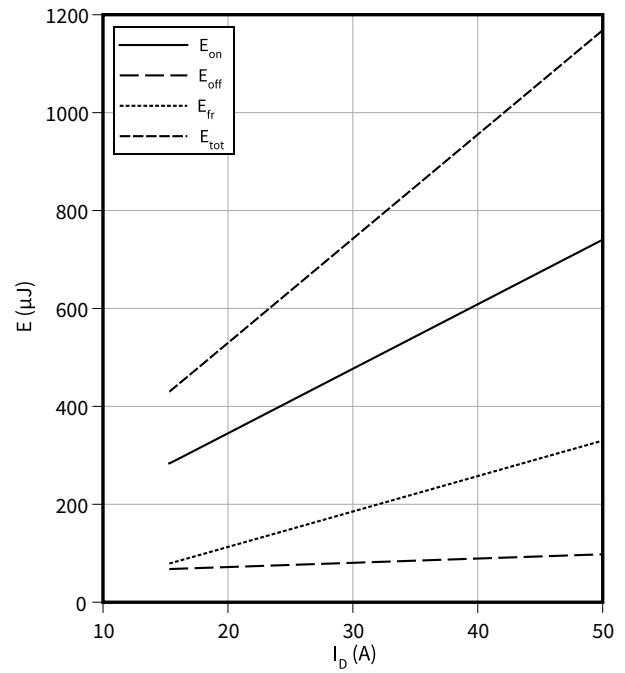
**Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(T_{vj})$   
 $V_{GS} = 0/18\text{ V}$ ,  $I_D = 25.6\text{ A}$ ,  $R_{G,ext} = 1\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$



**Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(I_D)$   
 $V_{GS} = 0/18\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $R_{G,ext} = 1\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$

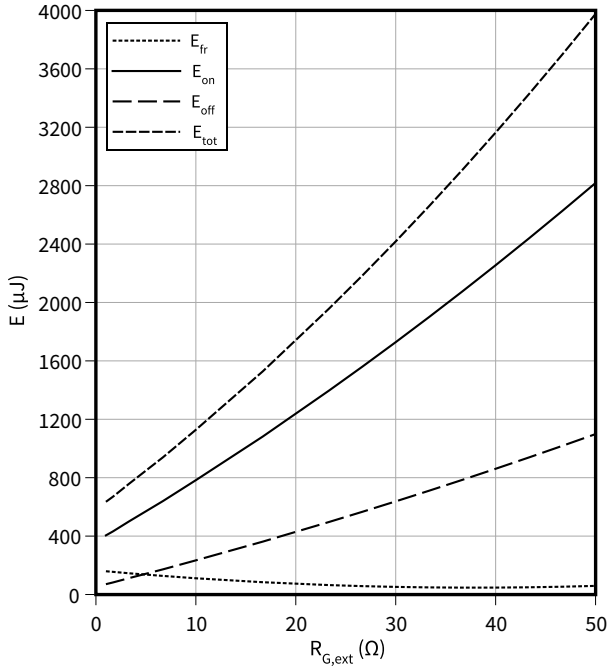


4 Characteristics diagrams

**Typical switching energy losses as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(R_{G,ext})$

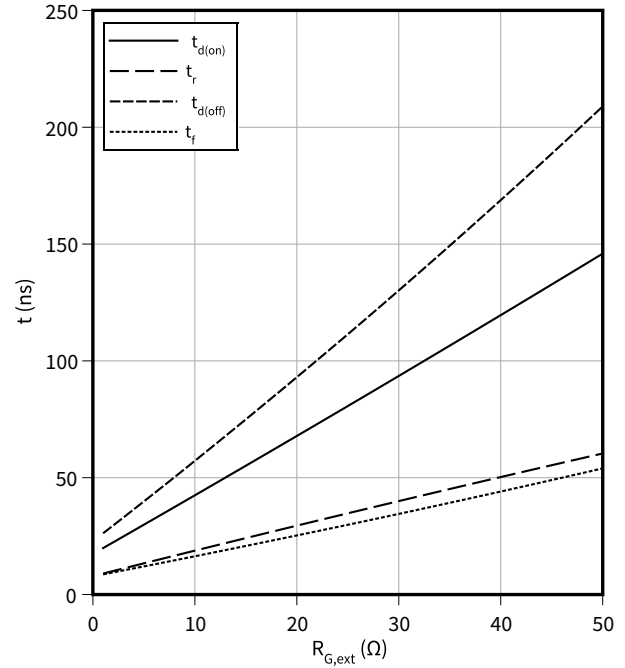
$V_{GS} = 0/18\text{ V}$ ,  $I_D = 25.6\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



**Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$t = f(R_{G,ext})$

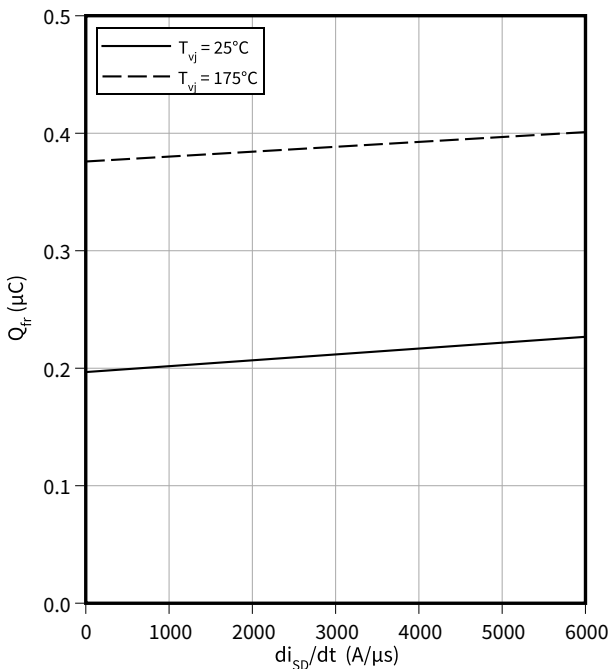
$I_D = 25.6\text{ A}$ ,  $V_{GS} = 0/18\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



**Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$Q_{fr} = f(di_{SD}/dt)$

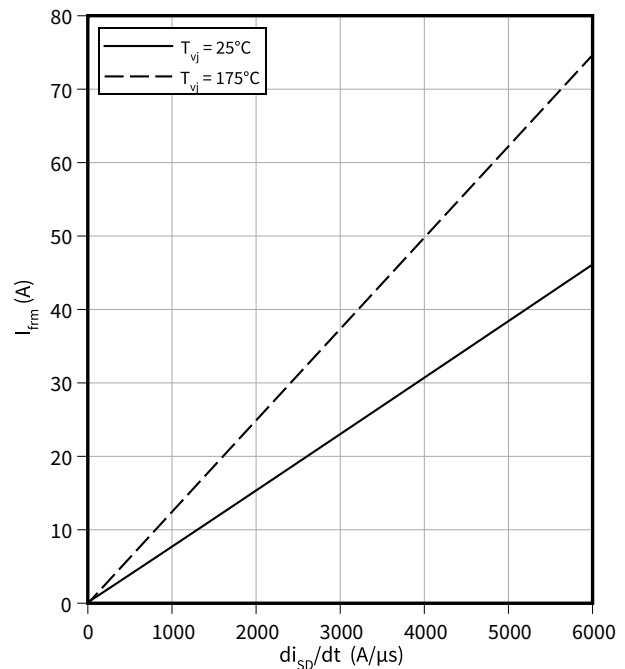
$V_{GS} = 0/18\text{ V}$ ,  $I_{SD} = 25.6\text{ A}$ ,  $V_{DD} = 800\text{ V}$



**Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$I_{frm} = f(di_{SD}/dt)$

$V_{GS} = 0/18\text{ V}$ ,  $I_{SD} = 25.6\text{ A}$ ,  $V_{DD} = 800\text{ V}$

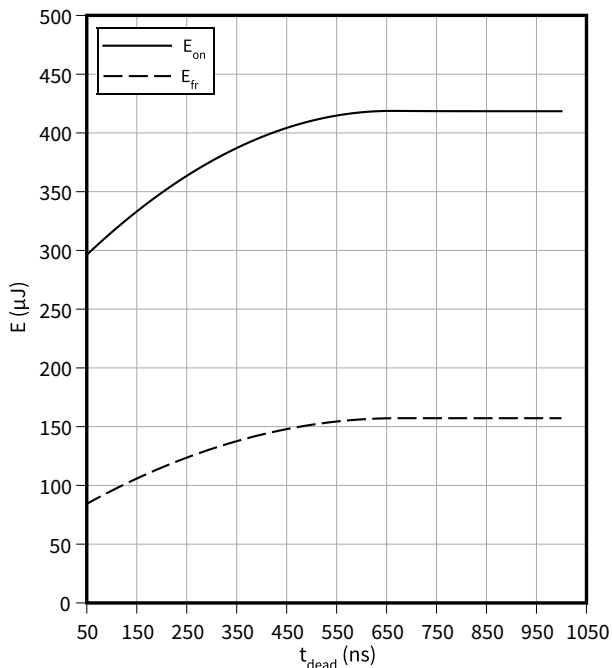


4 Characteristics diagrams

**Typical switching energy losses as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = -5$  V**

$$E = f(t_{dead})$$

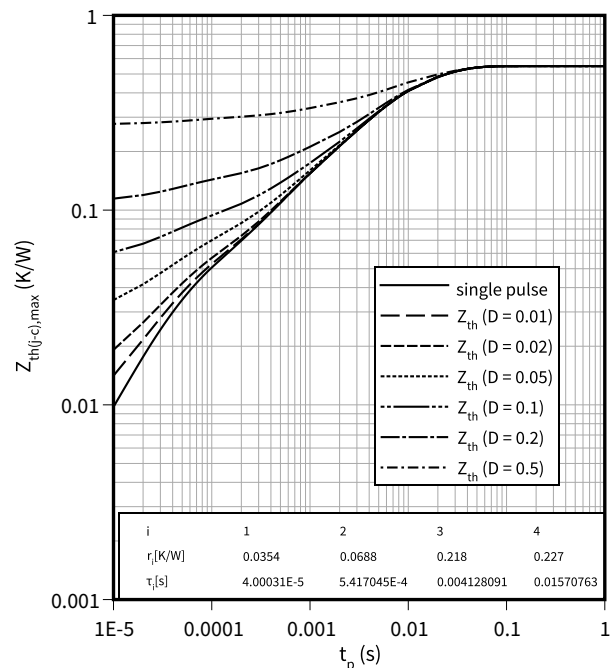
$V_{GS} = -5/18$  V,  $I_D = 25.6$  A,  $T_{vj} = 175$  °C,  $V_{DD} = 800$  V



**Max. transient thermal impedance (MOSFET/diode)**

$$Z_{th(j-c),max} = f(t_p)$$

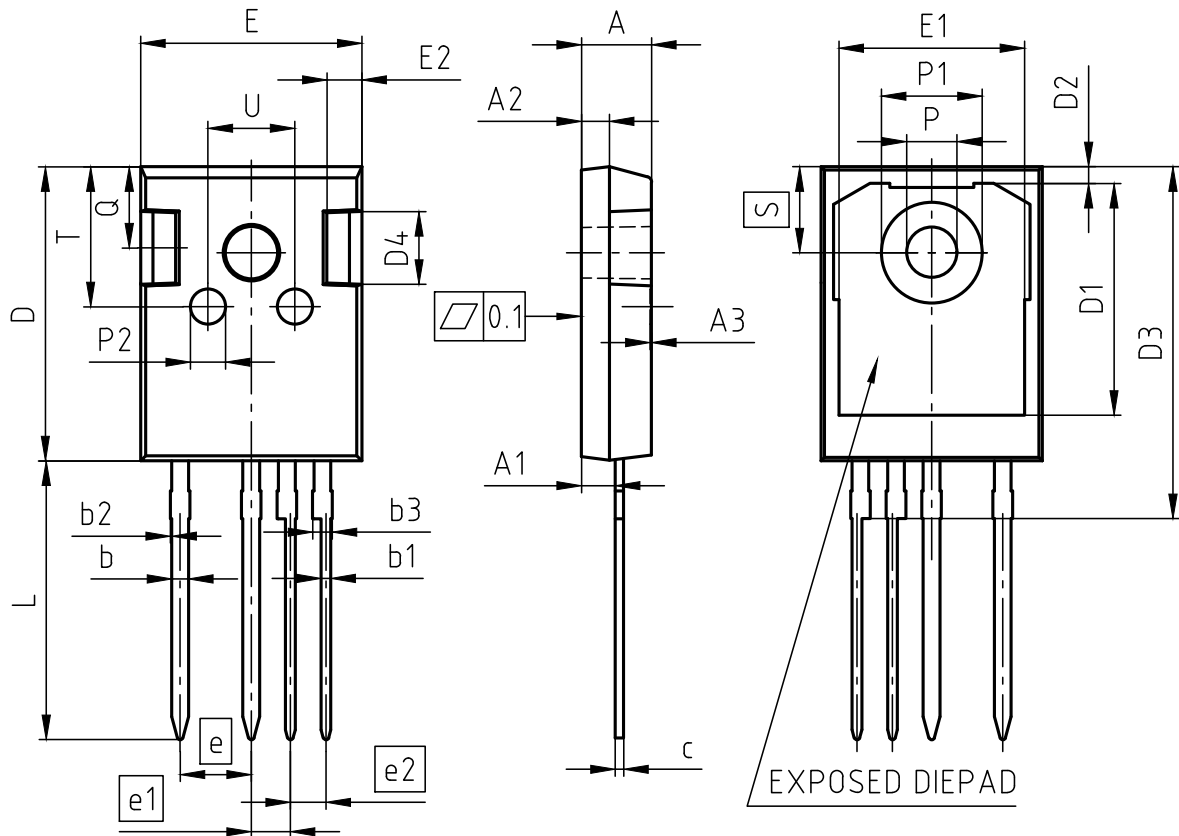
$$D = t_p/T$$



i	1	2	3	4
$r_l$ [K/W]	0.0354	0.0688	0.218	0.227
$\tau_l$ [s]	4.00031E-5	5.417045E-4	0.004128091	0.01570763

5 Package outlines

PG-TO247-4-STD-NT3.7



NOTES:  
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

PACKAGE - GROUP NUMBER:		PG-TO247-4-U02			
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.05	0.25	e	5.08	
b	1.10	1.30	e1	2.79	
b1	0.65	0.79	e2	2.54	
b2	---	0.20	N	4	
b3	1.34	1.44	L	19.80	20.10
c	0.58	0.66	øP	3.50	3.70
D	20.90	21.10	øP1	7.00	7.40
D1	16.25	16.85	øP2	2.40	2.60
D2	1.05	1.35	Q	5.60	6.00
D3	24.97	25.27	S	6.15	
D4	4.90	5.10	T	9.80	10.20
			U	6.00	6.40

Figure 1

## 6 Testing conditions

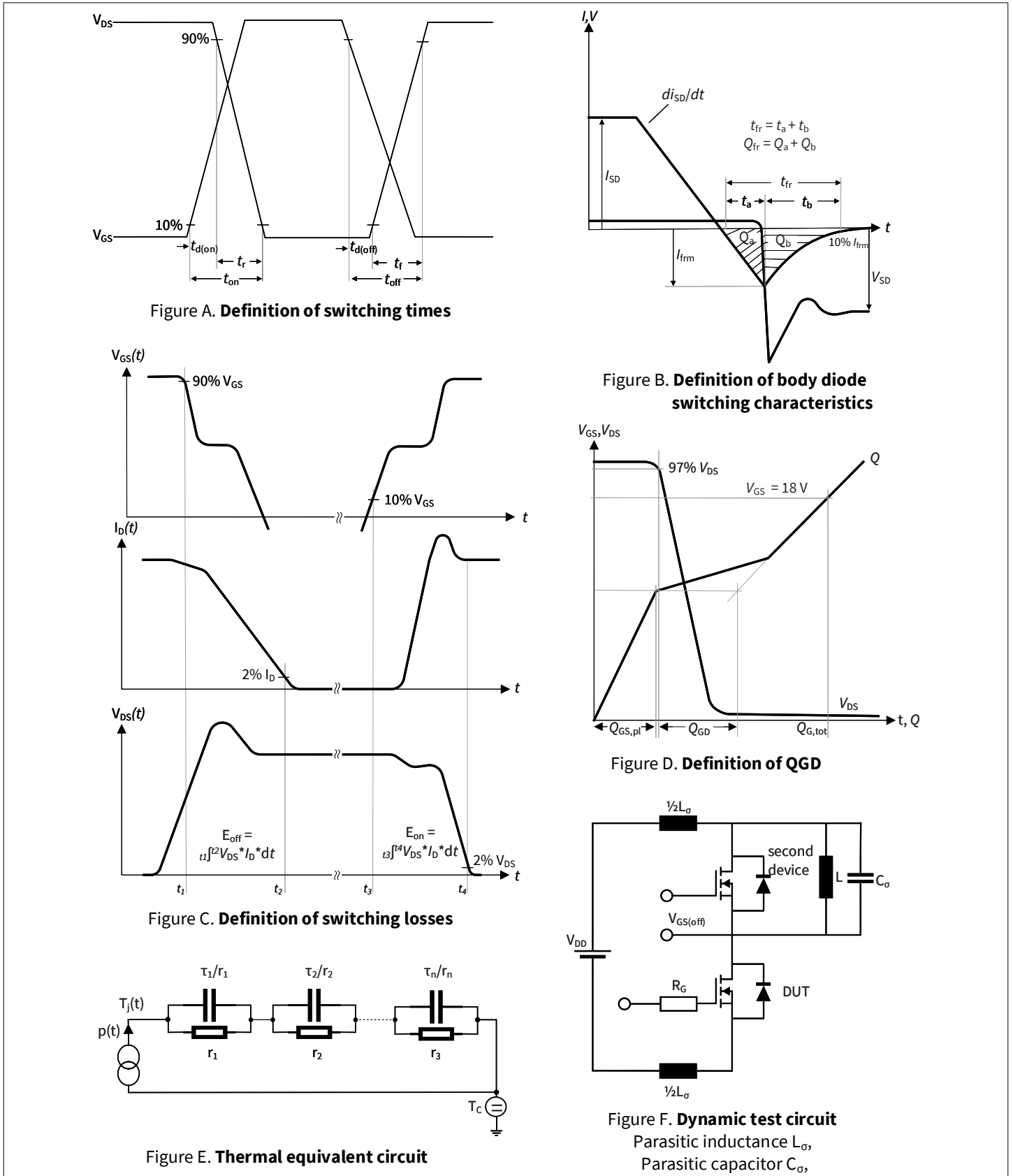


Figure 2

## Revision history

Document revision	Date of release	Description of changes
1.00	2022-02-03	Final datasheet
1.10	2022-08-10	Change of test condition of dynamic capacitances in Table 4, "Characteristic values" ( $C_{iss}$ , $C_{oss}$ , $C_{rss}$ ): $V_{DD}= 25\text{ V}$ to $V_{DD}= 800\text{ V}$ Correction of unit of "Input capacitance" $C_{iss}$ from nF to pF Change of $V_{GS}$ "Gate-source voltage, max. static voltage" in Table 2, "Maximum rated values" from -5/20 V to -7/20 V Editorial changes in "Features" on page 1 Editorial changes in "Package" on page 1 Correction of unit of x-axis at diagram "Max. transient thermal impedance (MOSFET/diode)" from $\mu\text{s}$ to s, on page 13 Correction of diagram "Max. transient thermal impedance (MOSFET/diode)", on page 13



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